

ABSTRACT

A semiconductor memory device according to an embodiment includes: a semiconductor layer extending in a first direction; a gate electrode layer including at least
5 one metal element selected from a group consisting of tungsten (W), molybdenum (Mo), and cobalt (Co); a charge storage layer provided between the semiconductor layer and the gate electrode layer; and a first insulating layer provided between the charge storage layer and the gate
10 electrode layer, the first insulating layer including a first region, the first region including aluminum (Al) and oxygen (O), the first insulating layer being in contact with the gate electrode layer.